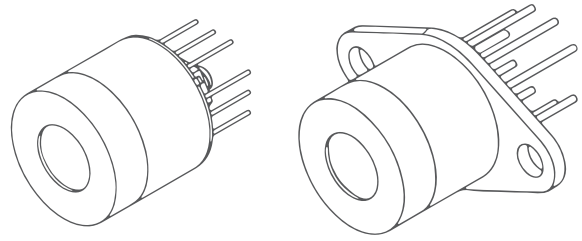


PV-8 SERIES

HgCdTe thermoelectrically cooled photovoltaic infrared detectors



4TE-TO8

4TE-TO66

FEATURES

- Spectral range: 3.0 to 10.0 μm
- Back-side illuminated
- Unique immersion lens technology applied
- No minimum order quantity required

APPLICATIONS

- Gas detection, monitoring and analysis: CH_4 , H_2S , NO_2 , SO_x
- FTIR spectroscopy

SERIES DESCRIPTION

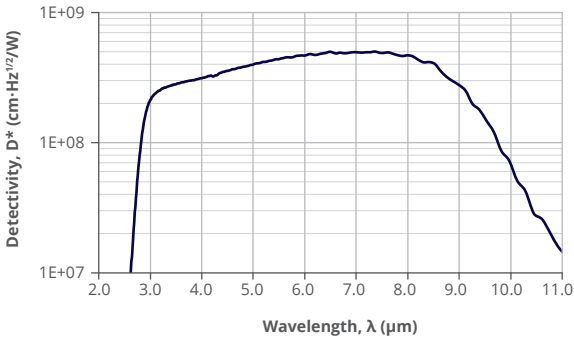
Detector symbol	Cooling (p. 191)	Temperature sensor (p. 192)	Active area, A, mm \times mm	Optical immersion	Package	Acceptance angle, Φ , deg.	Window (p. 193)
PV-4TE-8-0.1 \times 0.1-TO8-wZnSeAR-70	4TE $T_{\text{chip}}=198\text{K}$	thermistor	0.1 \times 0.1	no	TO8	~70	wZnSeAR (3 deg. zinc selenide, anti-reflection coating)
PV-4TE-8-0.1 \times 0.1-TO66-wZnSeAR-70					TO66		

SPECIFICATION ($T_{\text{amb}} = 293\text{K}$, $V_b = 0\text{V}$)

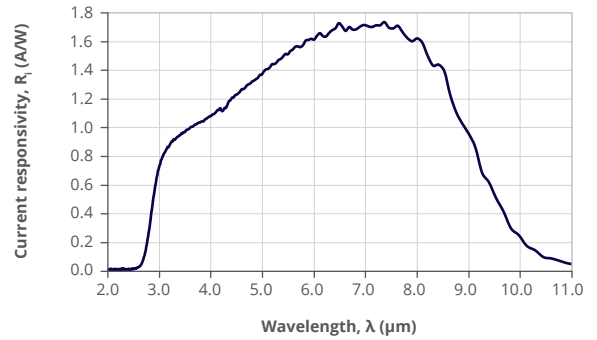
Detector symbol	Cut-on wavelength (10%)	Peak wavelength	Specific wavelength	Cut-off wavelength (10%)	Detectivity		Current responsivity			Time constant	Dynamic resistance	
	$\lambda_{\text{cut-on}}$	λ_{peak}	λ_{spec}	$\lambda_{\text{cut-off}}$	$D^*(\lambda_{\text{peak}}, 20\text{kHz})$	$D^*(\lambda_{\text{spec}}, 20\text{kHz})$	$R_i(\lambda_{\text{peak}})$	$R_i(\lambda_{\text{spec}})$		τ	R_d	
	μm	μm	μm	μm	$\text{cm}\cdot\text{Hz}^{1/2}/\text{W}$	$\text{cm}\cdot\text{Hz}^{1/2}/\text{W}$	A/W	A/W		ns	Ω	
	Typ.	Typ.	Typ.	Typ.	Typ.	Min.	Typ.	Min.	Typ.	Typ.	Min.	Typ.
PV-4TE-8-0.1 \times 0.1-TO8-wZnSeAR-70	3.0	6.5 \pm 1.0	8.0	10.0	5.0 \times 10 ⁸	4.0 \times 10 ⁸	1.9	1.5	1.7	45	50	100
PV-4TE-8-0.1 \times 0.1-TO66-wZnSeAR-70												

SPECTRAL RESPONSE (Typ., $T_{amb} = 293\text{ K}$)

PV-4TE-8-1x1-TO8/TO66-wZnSeAR-70



PV-4TE-8-1x1-TO8/TO66-wZnSeAR-70



MECHANICAL LAYOUT AND PINOUT

- 4TE-TO8 package
– Technical drawing (p. 209)
- 4TE-TO66 package
– Technical drawing (p. 211)

RECOMMENDED AMPLIFIERS

Detector symbol	Amplifier type
PV-4TE-8-0.1x0.1-TO8-wZnSeAR-70	AIP series (p. 126), PIP series (p. 129), MIP series (p. 132), SIP-TO8 series (p. 135), FIP series ^{*)} (p. 141)

^{*)} Only for biased detectors

ABSOLUTE MAXIMUM RATINGS

Parameter	Test conditions/remarks	Value	Unit
Ambient operating temperature, T_{amb}	Operation at $T_{amb} > 30^{\circ}\text{C}$ may increase the active element temperature and reduce the performance of the detector below specified parameters	-20 to 30	$^{\circ}\text{C}$
Storage temperature, T_{stg}		-20 to 50	$^{\circ}\text{C}$
Soldering temperature	Within 5 s or less	≤ 300	$^{\circ}\text{C}$
Storage humidity	No dew condensation	10 to 90	%
Maximum incident optical power density	Continuous wave (CW) or single pulses $> 1\ \mu\text{s}$ duration	100	W/cm^2
	Single pulses $< 1\ \mu\text{s}$ duration	1	MW/cm^2
Maximum bias voltage, $V_{b\ max}$	No bias voltage needed	-	-
Maximum TEC voltage, $V_{TEC\ max}$	4TE	8.3	V
Maximum TEC current, $I_{TEC\ max}$	4TE	0.4	A

Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. Constant or repeated exposure to absolute maximum rating conditions may affect the quality and reliability of the device.